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Vishay Siliconix

Automotive P-Channel 40 V (D-S) 175 °C MOSFET



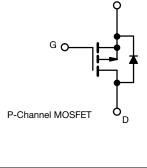
TO-263
S D
Top View G

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



PRODUCT SUMMARY	
V _{DS} (V)	-40
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0051
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0071
I _D (A)	-100
Configuration	Single
Package	TO-263



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-source voltage		V_{DS}	-40	V		
Gate-source voltage		V_{GS}	± 20	V		
Continuous drain current	$T_C = 25 ^{\circ}C^{a}$	I _D	-100			
Continuous drain current	T _C = 125 °C	чD	-72	İ		
Continuous source current (diode conduction) a	Is	-100	Α			
Pulsed drain current ^b	I _{DM}	-300				
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-41			
Single pulse avalanche energy	L = 0.1 IIII1	E _{AS}	84	mJ		
Maximum power dissipation ^b	T _C = 25 °C	P _D	150	W		
	T _C = 125 °C	r D	50	VV		
Operating junction and storage temperature ran	ige	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount c	R_{thJA}	40	°C/W		
Junction-to-case (drain)		R_{thJC}	1	C/VV		

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static		•				I.	<u> </u>	
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = -250 μA	-40	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-1.5	-	-2.5		
Gate-source leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}$	-	-	-1		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -40 V, T _J = 125 °C	-	-	-50	μΑ	
		V _{GS} = 0 V	V _{DS} = -40 V, T _J = 175 °C	-	-	-250		
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 \text{ V}$	-50	-	-	Α	
		V _{GS} = -10 V	I _D = -30 A	-	0.0042	0.0051	Ω	
But a survey state with a set		V _{GS} = -10 V	I _D = -30 A, T _J = 125 °C	-	-	0.0079		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -30 A, T _J = 175 °C	-	-	0.0094		
		V _{GS} = -4.5 V	I _D = -25 A	-	0.0059	0.0071		
Forward transconductance a	9fs	V _{DS} =	-15 V, I _D = -30 A	-	103	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{GS} = 0 V V _{DS} = -25 V, f = 1 MHz		11 063	14 500	pF	
Output capacitance	Coss	$V_{GS} = 0 V$			847	1110		
Reverse transfer capacitance	C _{rss}			-	757	1000	· ·	
Total gate charge ^c	Qg			-	185	280	nC	
Gate-source charge c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -20 \text{ V}, I_{D} = -50 \text{ A}$	-	25	-		
Gate-drain charge ^c	Q _{gd}			-	30	-		
Gate resistance	R_g		f = 1 MHz		3.6	5.4	Ω	
Turn-on delay time ^c	t _{d(on)}			-	15	25		
Rise time ^c	t _r	V_{DD} = -20 V, R_L = 0.4 Ω $I_D \cong$ -50 A, V_{GEN} = -10 V, R_g = 1 Ω		-	180	280	ns	
Turn-off delay time ^c	t _{d(off)}			-	145	220		
Fall time ^c	t _f			-	160	250		
Source-Drain Diode Ratings and Char	acteristics ^b	•			•			
Pulsed current ^a	I _{SM}			-	-	-300	Α	
Forward voltage	V_{SD}	le =	-	-0.84	-1.5	V		

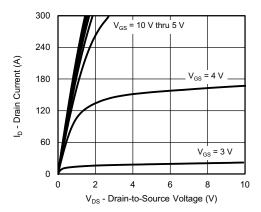
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

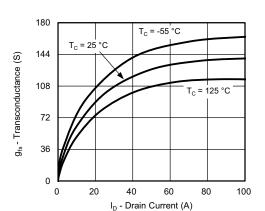
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



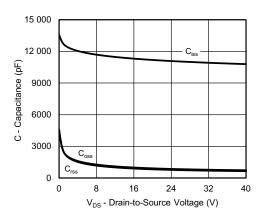
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



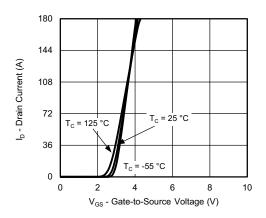
Output Characteristics



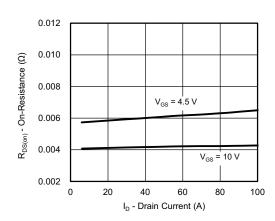
Transconductance



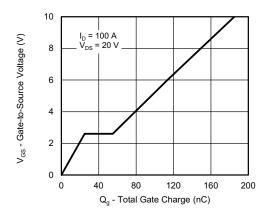
Capacitance



Transfer Characteristics



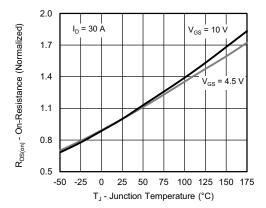
On-Resistance vs. Drain Current



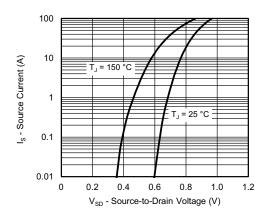
Gate Charge



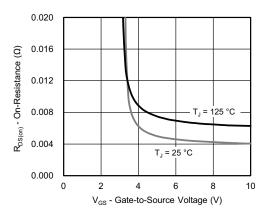
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



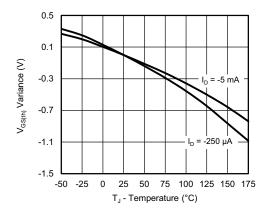
On-Resistance vs. Junction Temperature



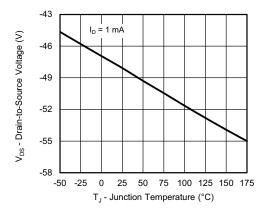
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



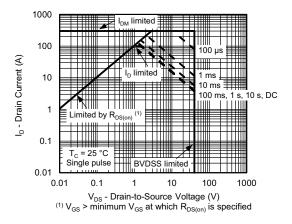
Threshold Voltage



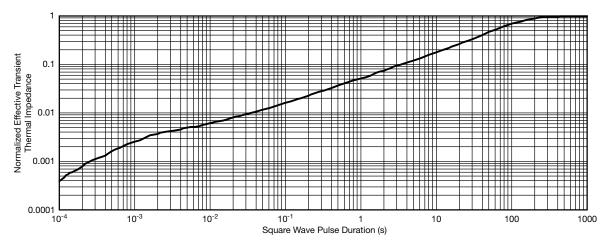
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



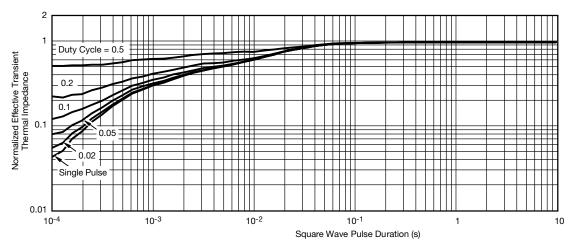
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg275728.



TO-263 (D²PAK): 3-LEAD









DETAIL A (ROTATED 90°)



⋝:	,	 	b— b1–		ļ	ļ
2:	П				5	ပ
	SE	СТ	ION	ΙΔ.	- 1 - Δ	Ŧ

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

		INCHES		MILLIN	LIMETERS	
	DIM.	MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54	BSC	
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254	BSC	
М		-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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